

**MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA**

Photo Detector Chip Diode Output

The MFODC1100WP is designed for infrared radiation detection in high frequency Fiber Optic Systems.

- Fast Response ~ 1 ns Max
- Anode/Cathode Metallization Compatible with Conventional Wire and Die Bonding Techniques
- Available in Chip or Wafer Form

MFODC1100WP

FIBER OPTICS
PHOTO DETECTOR
CHIP
DIODE OUTPUT

MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value		Unit
Reverse Voltage	V_R	50		Volts
Power Dissipation(1)	P_D	50		mW
Operating Junction Temperature Range	T_J	-65 to +125		°C
Storage Temperature Range	T_{stg}	-65 to +200		°C

STATIC ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
Dark Current ($V_R = 5 \text{ V}$, $R_L = 1 \text{ M}\Omega$, $H = 0$)	I_D	—	—	1	nA
Reverse Breakdown Voltage ($I_R = 10 \mu\text{A}$)	$V_{(BR)R}$	50	—	—	Volts
Forward Voltage ($I_F = 50 \text{ mA}$)	V_F	—	0.7	1	Volts
Junction Capacitance ($V_R = 5 \text{ V}$, $f = 1 \text{ MHz}$)	C_j	—	—	2	pF

OPTICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Radiation Responsivity ($V_R = 5 \text{ V}$, $\lambda = 850 \text{ nm}$, $P = 10 \mu\text{W}$)	R	0.3	0.4	—	$\mu\text{A}/\mu\text{W}$
Response Time ($V_R = 5 \text{ V}$, $\lambda = 850 \text{ nm}$)	t_r, t_f	—	0.5	1	ns

DIE SPECIFICATIONS

Die Size Mils	Die Thickness Mils	Bond Pad Size Mil		Metallization		Active Area Square Mil
		Anode	Cathode	Front(2)	Back(3)	
30 x 30	8-10	4 dia.	30 x 30	Al	Au	154

NOTES: 1. Maximum power dissipation rating is determined with chip mounted on a header or lead frame using conventional Motorola Semiconductor assembly techniques.

2. Thickness — a minimum of 10,000 Å.

3. Thickness — a minimum of 15,000 Å.

Active
Area

A

Back = Cathode

A = Anode

10

MFODC1100WP

TYPICAL CHARACTERISTICS

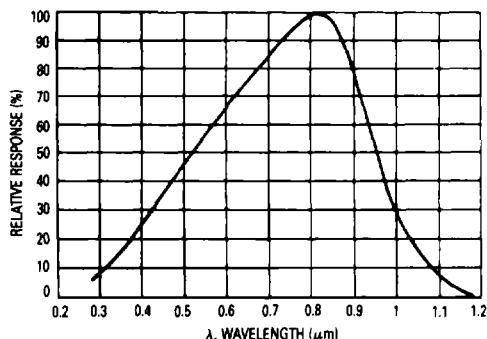


Figure 1. Relative Spectral Response

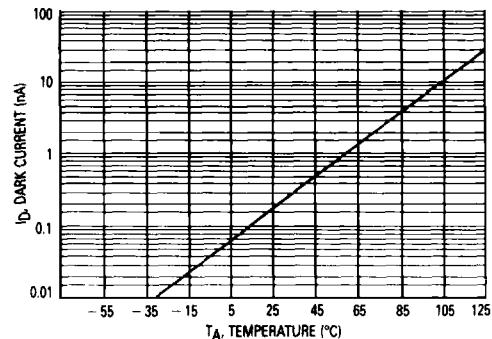


Figure 2. Dark Current versus Temperature

ORDERING INFORMATION

This die is available with the packaging and visual inspection listed below.

TABLE 1

Die Type Suffix	Packaging	Description	Visual Inspection
WP	Wafer Pak	Wafer-probed, unscribed, unbroken and heat sealed in plastic bag (rejects are inked)	Visual inspected by sample to a LTPD = 10